Ultra-high-resolution PµSL Based 3D Printing and Its Applications

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The trend of miniaturization is evident in a growing number of industries as the demand for smaller parts for medical devices, consumer electronics and robotics grows. Many industries are faced with challenges in manufacturing parts with complex geometries with detailed features and excellent surface quality. While 3D printing has rapidly advanced in recent decades, drawbacks such as resolution and throughput have limited its widespread adoption within certain applications where tight tolerance and high level of customization are required. BMF's unique printing technology, named PuSL (Projection Micro Stereolithography) is set out to remove these technological barriers, offering industrial designers and engineers a way to rapidly prototype and batch produce high value components¹. Compared to traditional manufacturing methods such as injection molding and CNC machining, PuSL substantially reduces the cost and lead time by avoiding laborious and tedious fabrication processes. By leveraging light, customized optics, a high-precision printing platform and controlled processing technology, P μ SL can achieve down to 2um resolution with $\pm 10\mu$ m tolerance and a practical build volume up to $50 \times 50 \times 50$ mm. In this talk, we will introduce the working principles and advantages of PuSL and highlight some recent examples of PuSL enabled applications, from microneedles to 3D scaffolds for tissue engineering.



Fig 1. 3D printed samples prepared by $P\mu$ SL. (a) 3D capillary ratchet with dual reentrant curvatures². (b) Microneedle platform with multiple channels inside each needle³. (c, c') Pine needle–inspired asymmetric pillars for droplet transportation⁴.

¹ Ge Q. et al Int. J. Extrem. Manuf. **2** 022004 (2020).

² Feng S. et al *Science* **373** *6561*, *1344-1348* (2021).

³ Lin L. et al *Adv. Funct. Mater. 2109187 (2021)*.

³ Feng S. et al *Science Advances*. **6** *28 (2020)*.